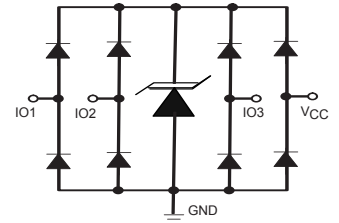
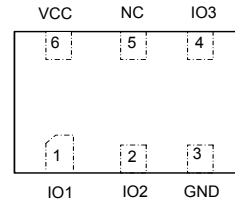


Features

- 40Watts peak pulse power ($t_p = 8/20\mu s$)
- DFN1510-6 package
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Ultra low capacitance (0.35pF typical I/O to I/O)
- ESD Protection for high-speed data lines to:
 - IEC 61000-4-2 $\pm 20kV$ contact $\pm 25kV$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 4A (8/20 μs)



Mechanical Data

- **Case:** DFN1510-6 (plastic package).
Lead free; RoHS compliant; Halogen free
- **Molding Compound Flammability Rating:**
UL 94 V-0
- **Terminals:** High temperature soldering guaranteed:
260 °C/10 sec. at terminals

Applications

- SDIO
- USB 2.0, MHL
- SCGA Video Connections
- Precision Analog Interface
- Notebooks, Desktops, and Server

Absolute Maximum Ratings

Ratings at 25 °C, ambient temperature unless otherwise specified

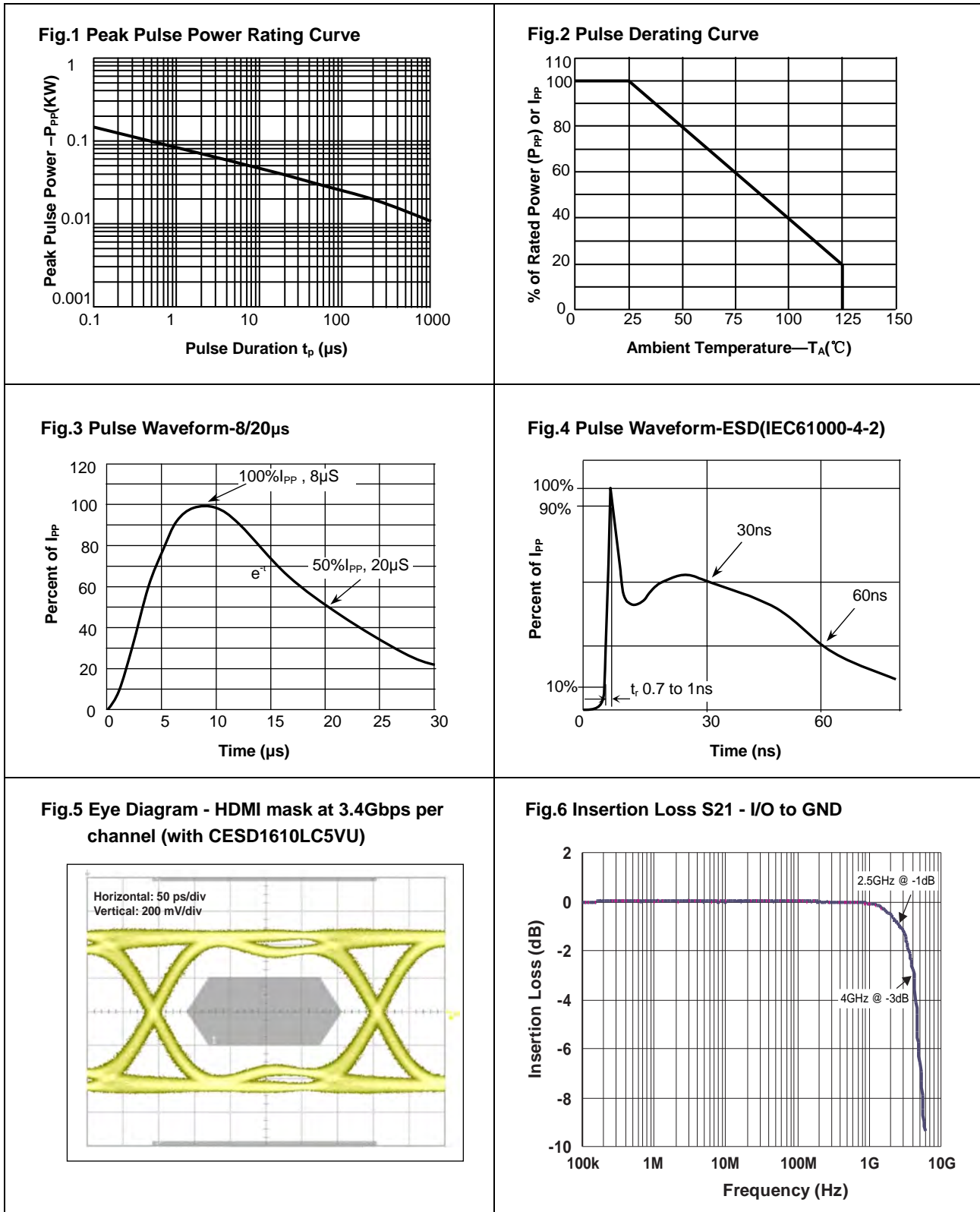
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_p=8/20\mu s$)	P_{PP}	40	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	20/25	kV
Peak Pulse Current ($t_p = 8/20\mu s$)	I_{PP}	4.0	A
Junction Temperature	T_J	-55 to +125	°C
Storage temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

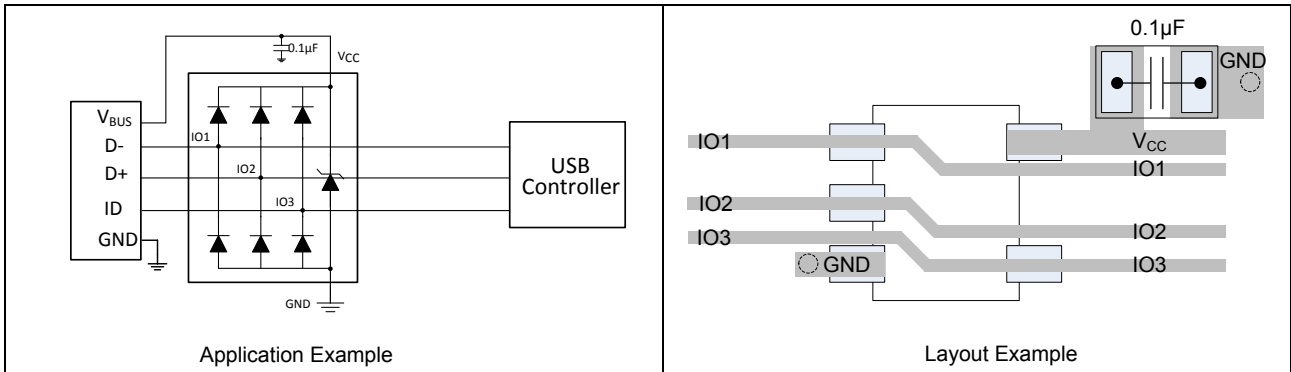
($T_A = 25\text{ °C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}				5	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	6.0		8.5	V
Reverse Leakage Current	I_R	$V_R=5V$		0.1	0.2	μA
Clamping Voltage(SURGE)	V_C	$I_{PP}=4A, T_p=8/20\mu s$		10		V
Clamping Voltage(ESD)	V_C	$V_{ESD} = +8kV$		12		V
Junction Capacitance	C_J	$V_R=0V, f=1MHz, I/O$ to I/O		0.35		pF
	C_J	$V_R=0V, f=1MHz, I/O$ to GND		0.5		pF

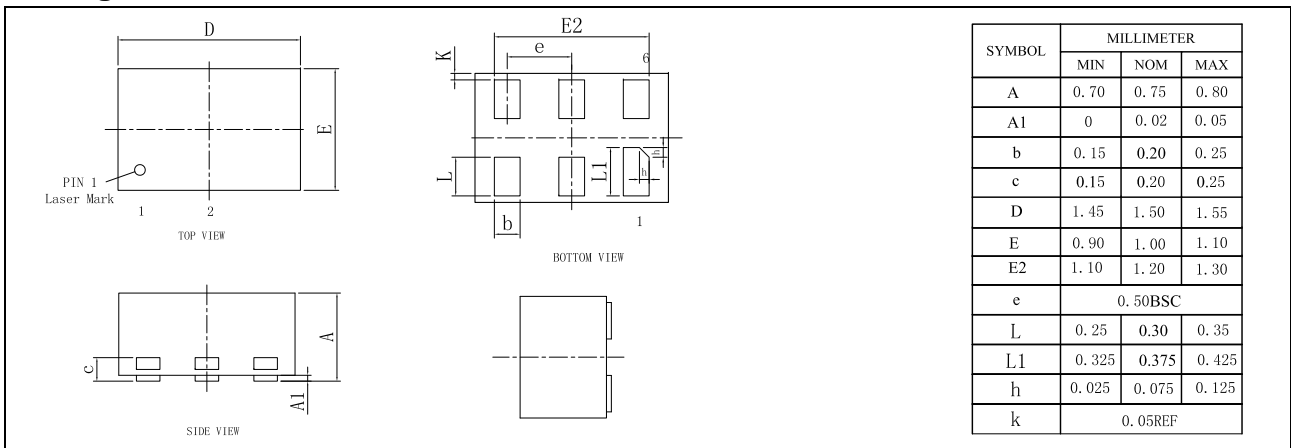
Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)



Typical Application



Package Dimensions



Marking



Ordering information

Order code	Package	Packaging option	Base quantity	Packaging specification
YEU15C60504AV	DFN1510-6	Tape and reel	3000pcs / reel	EIA STD RS-481